

Abstract

[0036] A heterojunction bipolar transistor (HBT), comprises a collector formed over a substrate, a base formed over the collector, an emitter formed over the base, and a tunneling suppression layer between the collector and the base, the tunneling suppression layer fabricated from a material that is different from a material of the base and that has an electron affinity equal to or greater than an electron affinity of the material of the base.

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